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▶ Products ▶ ▶ UHF broad	dcast power transistors (470-8	OU MHZ) PBLF884P		Applications	Looking for
BLF884P	▶ Preview	Product information i	▶ Selection guide 4		
Datasheet	UHF power LDMOS	transistor			
No datasheet available	General description	Pinning information	Quality/reliability/chemical		
Notify me when datasheet becomes available	 Features and benefits Applications Quick reference Similar Products 	 Block diagrams Pricing/ordering/availability Samples Products/packages 	content Design support Print/email Disclaimers		
	All information hereunder is	subject to the subsequent disclaimers			
General description					Hide 🥅

A 350 W LDMOS RF power transistor for broadcast transmitter applications and industrial applications. The excellent ruggedness of this device makes it ideal for digital and analog transmitter applications.

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Features and benefits Compliant to Directive 2002/95/EC, regarding RoHS 22 Designed for broadband operation (470 MHz to 860 MHz) 22 Easy power control 22 Excellent reliability Excellent ruggedness High efficiency 22

High power gain

Applications

- Internal input matching for high gain and optimum broadband operation 22
- 22 Optimum thermal behavior and reliability, $R_{th(j-c)} = 0.22$ K/W

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Communication transmitter applications in the UHF band

Industrial applications in the UHF band

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Quick refei	rence					Hide F
Symbol	Parameter	Conditions	Min	Typ/Nom	Max	Unit
f _{range}	frequency range		470		860	MHz
Mode of op	peration: DVB-T (8K OFDM)					
P _{L(AV)}	average output power	V _{DS} = 50 V; f = 858 MHz	70			W
G _p	power gain	V _{DS} = 50 V; f = 858 MHz	20	21		dB
η _D	drain efficiency	$V_{DS} = 50 \text{ V}; \text{ f} = 858 \text{ MHz}; \text{ I}_{Dq} = 0.65 \text{ A}$	30	33		%
I _{Dq}	quiescent drain current	$V_{DS} = 50 V$		0.65		А
IMD _{shldr}	intermodulation distortion shoulder	f = 858 MHz		-31	-27	dBc
PAR	peak-to-average ratio	f = 858 MHz		8.2		dB

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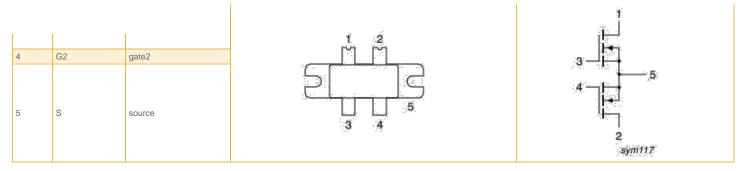
Similar Products

BLF884P links to the similar products page containing an overview of products that are similar in function or related to the type number(s) as listed on this page. The similar products page includes products from the same catalog tree(s), relevant selection guides and products from the same functional category.

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Pinning i	information			Hide 🖵
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D1	drain1		
2	D2	drain2		
3	G1	gate1		

UHF power LDMOS transistor from NXP Semiconductors



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Pricing/ordering/availability Hide								Hide 🥅	
Type number	Ordering code(12NC)	Orderable part number	Region	Distributor	In stock	Order quantity	Inventory date	Buy online	Samples
BLF884P	9340 656 55112	BLF884P,112							not available

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Products/packages							
Type number	Orderable part number	Ordering code (12NC)	Product status	Package	Packing	Marking	ECCN
BLF884P	BLF884P,112	9340 656 55112	Development	SOT1121A (CDFM4)	Bulk Pack	Standard Marking	

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Quality/reliability/chemical content									
Type number	Orderable part number	Chemical content	RoHS	Leadfree conversion date	RHF	IFR (FIT)	MTBF (hours)	MSL	MSL LF
BLF884P	BLF884P,112	BLF884P	EU/CN ROHS COMPLIANT D	Always Pb-free	D			NA	NA

Quality and reliability disclaimer

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